

## Silicon PNP Power Transistors

2SA768

## DESCRIPTION

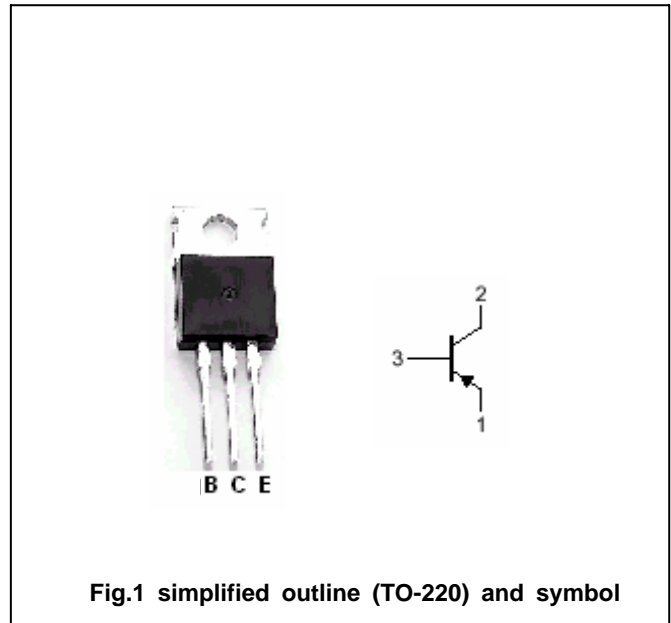
- With TO-220 package
- Complement to type 2SC1826

## APPLICATIONS

- For low frequency power amplifier applications

## PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector; connected to mounting base
3	Base

Absolute maximum ratings( $T_a=25^{\circ}\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-60	V
$V_{CEO}$	Collector-emitter voltage	Open base	-60	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-4	A
$P_C$	Collector power dissipation	$T_C=25^{\circ}\text{C}$	30	W
$T_j$	Junction temperature		150	$^{\circ}\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^{\circ}\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-25mA, I <sub>B</sub> =0	-60			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-1mA, I <sub>E</sub> =0	-60			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-3A; I <sub>B</sub> =-0.3A			-1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-3A; I <sub>B</sub> =-0.3A			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-60V; I <sub>E</sub> =0			-10	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-10	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-1A; V <sub>CE</sub> =-4V	60		240	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A; V <sub>CE</sub> =-10V		10		MHz

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance:  $\pm 0.10$  mm)